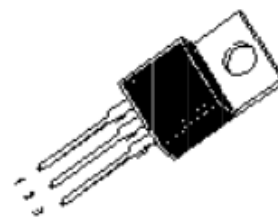


# IRFZ44

# MOSFET

- **Packaging form:**  
TO-220

TO-220



1.T1 阳极1 2. 阴极 2 3.控制极

- **extreme:**

| The parameter name        | symbol    | rating   | unit        |
|---------------------------|-----------|----------|-------------|
| drain-source voltage      | $V_{DS}$  | 55       | V           |
| Grid source voltage       | $V_{GS}$  | $\pm 20$ | v           |
| drain current             | $I_D$     | 8.5      | A           |
| The highest work is warm  | $T_J$     | 175      | $^{\circ}C$ |
| Storage temperature range | $T_{stg}$ | -55~+175 | $^{\circ}C$ |

- **Electrical characteristics ( $T_a=25^{\circ}C$ )**

| parameter                                     | symbol       | test condition                  | least value | representative value | crest value | unit       |
|---|--------------|---------------------------------|-------------|----------------------|-------------|------------|
| The leakage source breaks through the voltage | $BV_{DSS}$   | $V_{GS} = 0V, I_D = 250mA$      | 55          | --                   | --          | V          |
| The gate opens the voltage                    | $V_{th(GS)}$ | $I_D = 250mA, V_{DS} = V_{GS}$  | 1.4         | 1.9                  | 2.5         | V          |
| Grid source leakage current                   | $I_{GSS}$    | $V_{GS} = \pm 20V, V_{DS} = 0V$ | --          | --                   | $\pm 100$   | nA         |
| Leakage source saturation leakage current     | $I_{DSS}$    | $V_{DS} = 55V, V_{GS} = 0V$     | --          | --                   | 1.0         | mA         |
|   |              | $I_D = 8.5A, V_{GS} =$          | --          | 14                   | 20          | m $\Omega$ |

|   |                     |   |    |    |      |    |
|---|---------------------|---|----|----|------|----|
| Lease source conduction resistance                    | R <sub>DS(on)</sub> | 10V                                       |    |    |      |    |
|   |                     | I <sub>D</sub> =6A ,V <sub>GS</sub> =4.5V | -- | 20 | 29.5 | mΩ |
| Lesource parasitic diode positive guide pressure drop | v <sub>SD</sub>     | I <sub>S</sub> =8.5A ,V <sub>GS</sub> =0V | -- | -- | 1.4  | V  |